

A 10-bit Linearity Current-Controlled Ring Oscillator with Rolling Regulation for Smart Sensing

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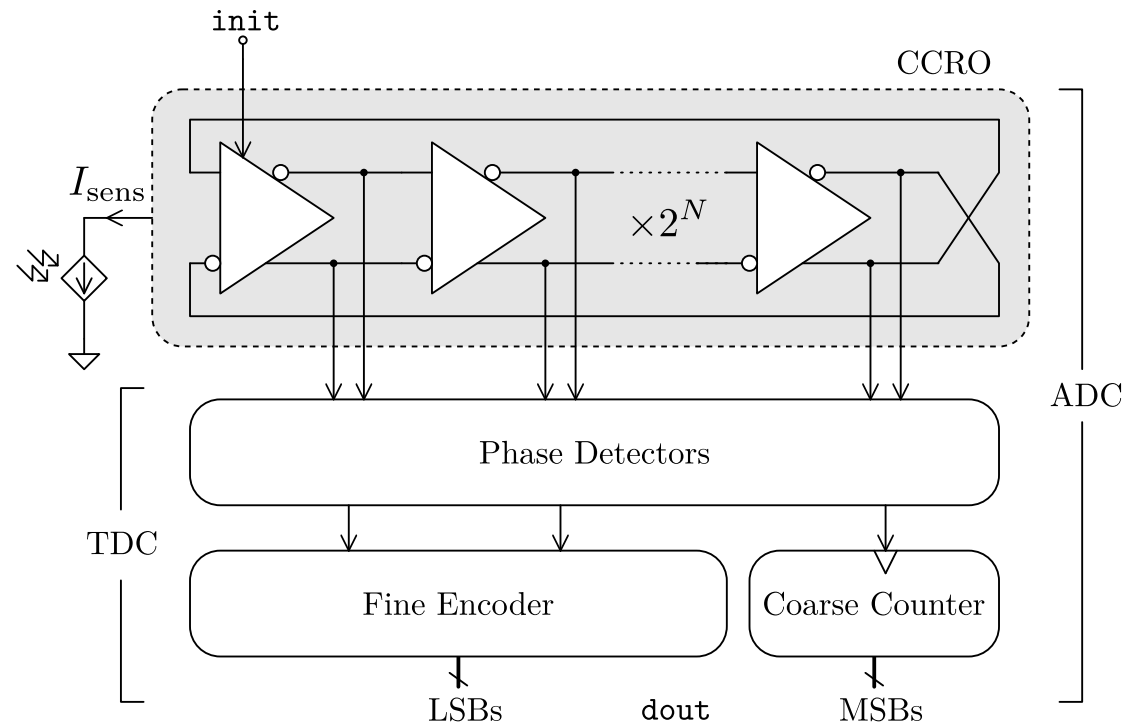
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- 2 CCRO Non-Linearity Issues
- 3 Rolling Regulation Proposal
- 5 Design Example in 0.18 μm CMOS Technology
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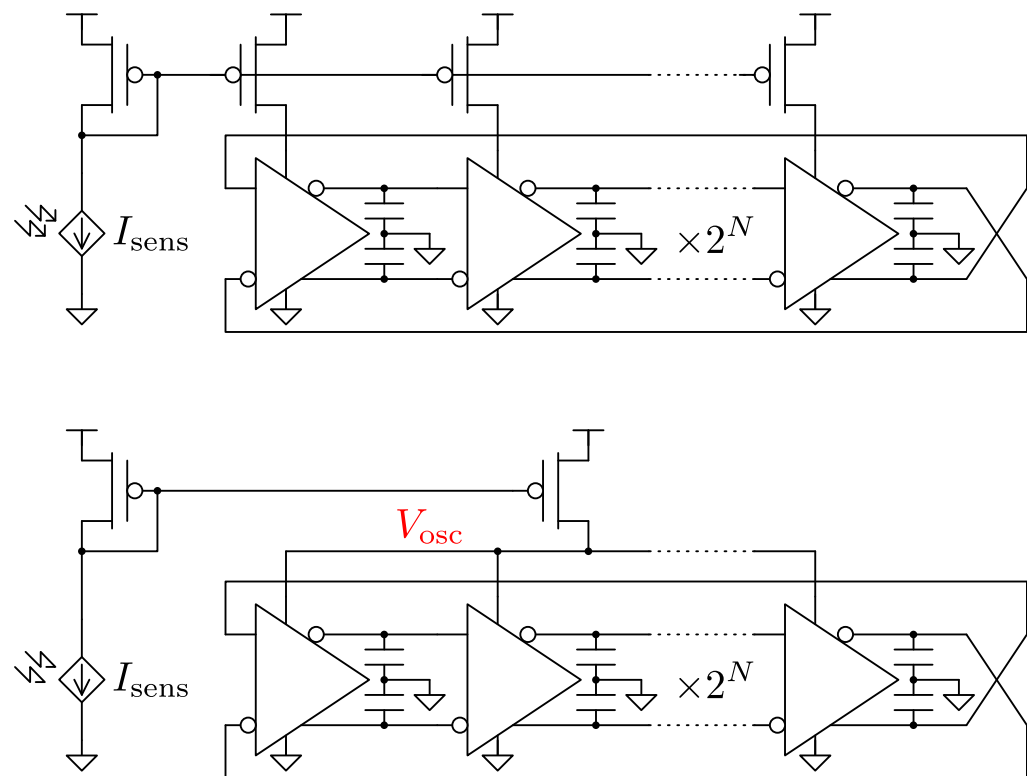
Introduction

- ▶ **Time-domain** processing for low-voltage digital-like ADCs
- ▲ Current-controlled ring oscillator (**CCRO**) to interface with current-mode sensors (e.g. optical, chemical)
- ▲ **Coarse/fine** architectures for low-power operation



Introduction

- ▶ **Time-domain** processing for low-voltage digital-like ADCs
- ▲ Current-controlled ring oscillator (**CCRO**) to interface with current-mode sensors (e.g. optical, chemical)
- ▲ **Coarse/fine** architectures for low-power operation
- ▶ Classic **current-starving** circuit implementation
- ▲ **Current steering** to improve uniformity of fine quantization
- ▼ Signal dependency of CCRO rail voltage (V_{osc}) causes I-to-F **non-linearity**

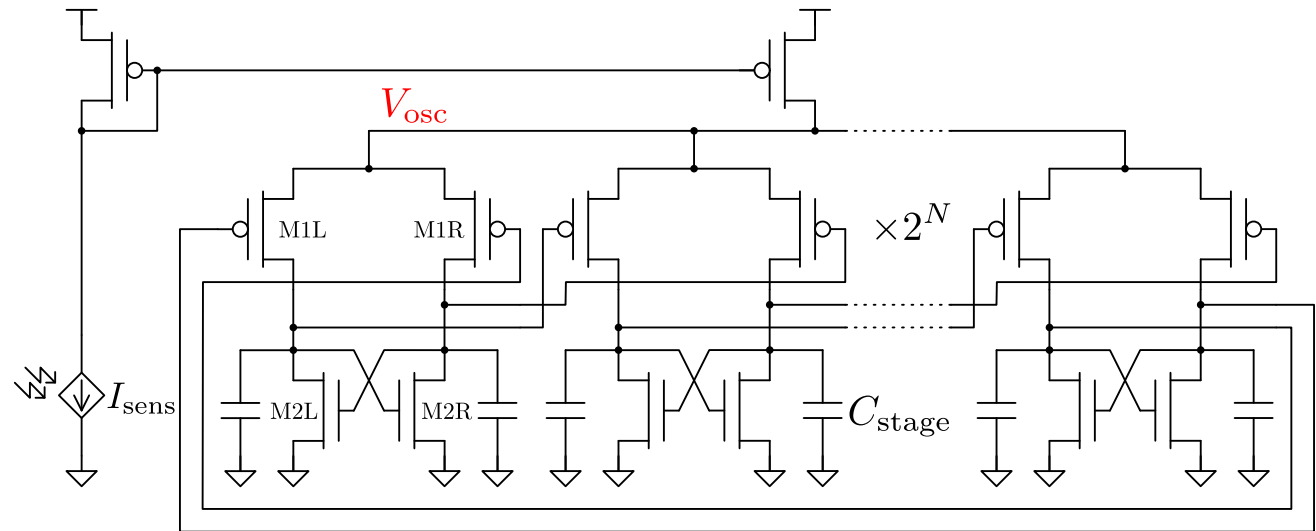


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CCRO Non-Linearity Issues

- **Differential** latch (M1,2) with symmetrical load capacitance (C_{stage})

$$f_{\text{osc}} \propto \frac{I_{\text{sens}}}{C_{\text{stage}} V_{\text{osc}}}$$

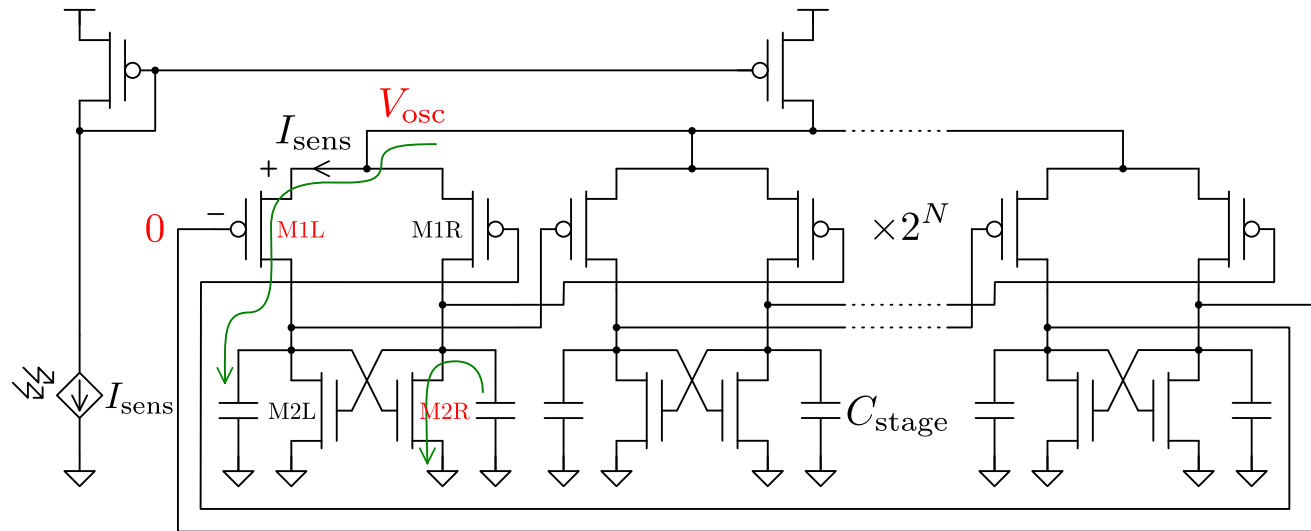


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$$f_{\text{osc}} \propto \frac{I_{\text{sens}}}{C_{\text{stage}} V_{\text{osc}}}$$

- PMOS transistors define **rail voltage**:



$$V_{\text{osc}} = \left(1 - \frac{1}{n}\right) V_{\text{DD}} + \frac{V_{\text{TO1}}}{n} + \sqrt{\frac{2I_{\text{sens}}}{n\beta_1}}$$

$$f_{\text{osc}} \propto \frac{\frac{I_{\text{sens}}}{I_{\text{S1}}}}{1 + \frac{1}{n} \left(\frac{V_{\text{TO1}}}{V_{\text{DD}}} - 1\right) + 2 \frac{U_t}{V_{\text{DD}}} \sqrt{\frac{I_{\text{sens}}}{I_{\text{S1}}}}}$$

$$\begin{cases} I_{\text{D}} = \frac{\beta}{2n} (V_{\text{GB}} - V_{\text{TO}} - nV_{\text{SB}})^2 \\ I_{\text{S}} = 2n\beta U_t^2 \end{cases} \quad \begin{array}{l} \text{EKV model in} \\ \text{strong inversion} \\ \text{forward saturation} \\ (V_{\text{B}} \doteq V_{\text{DD}}) \end{array}$$

CCRO Non-Linearity Issues

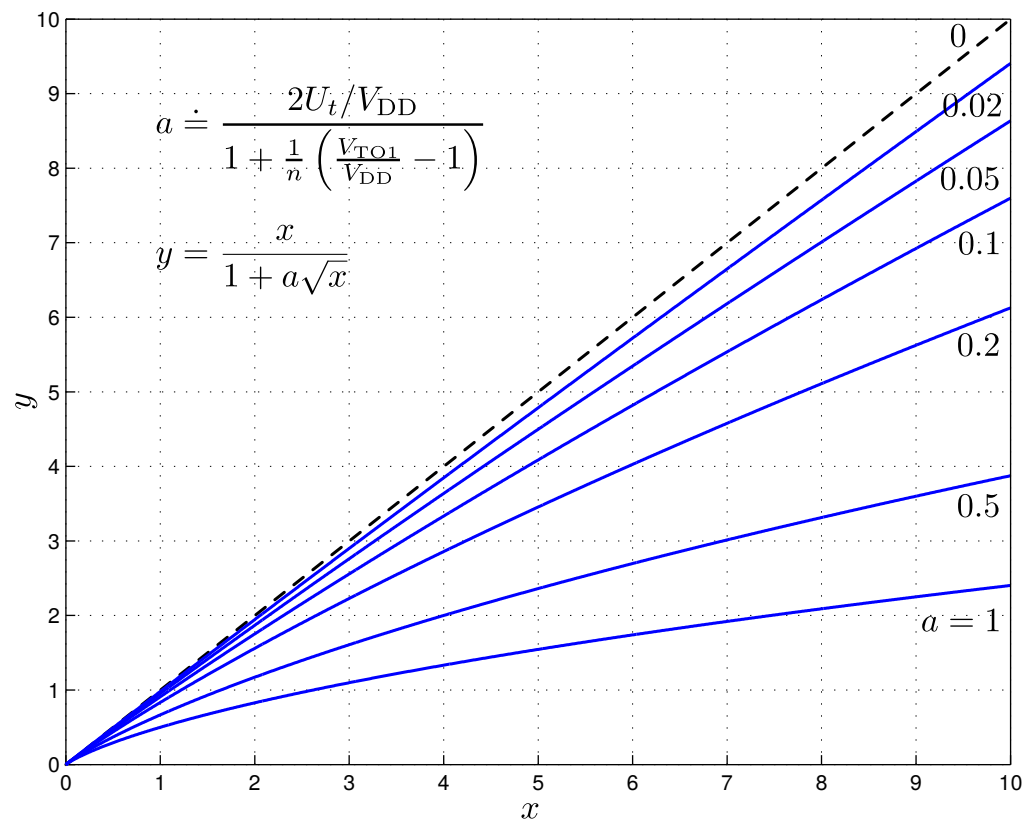
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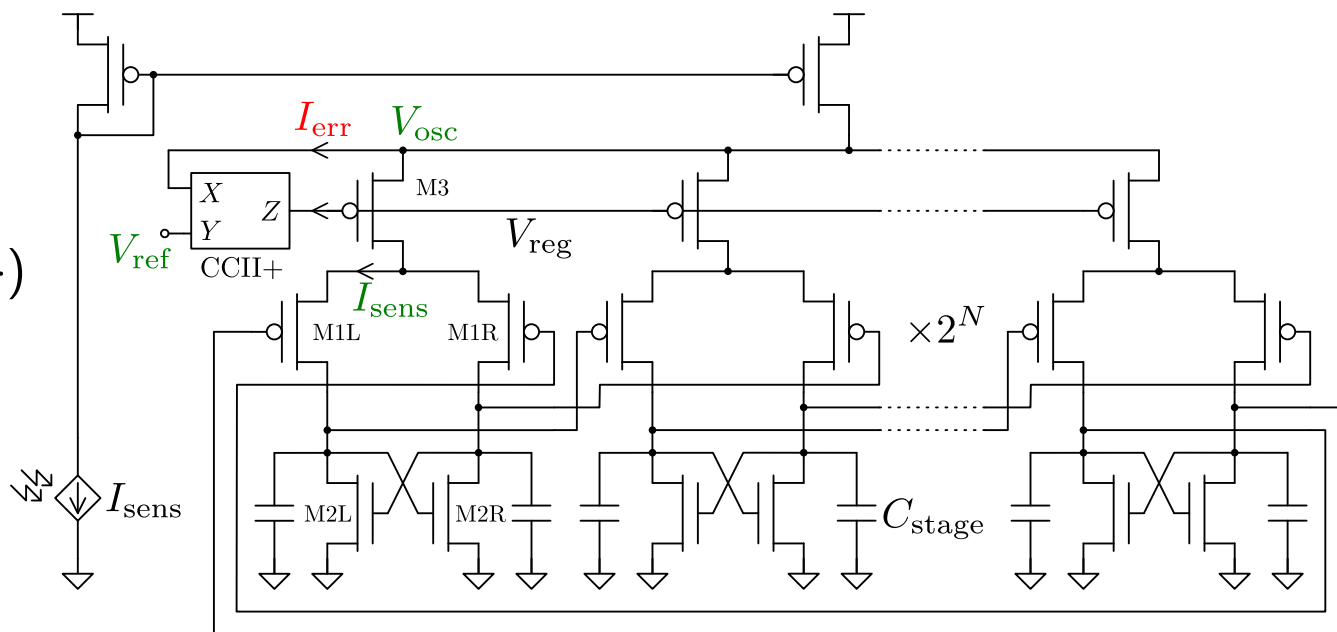


- ▼ Strong non-linearities for **high-current** full scale or **low-voltage** operation

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CCRO with Rolling Regulation

- ▶ Series transistor (**M3**) to regulate rail voltage independently from signal current
- ▶ Second generation current conveyor (**CCII+**) as **common** control



- ▲ Rail voltage **regulation** + signal current **steering**

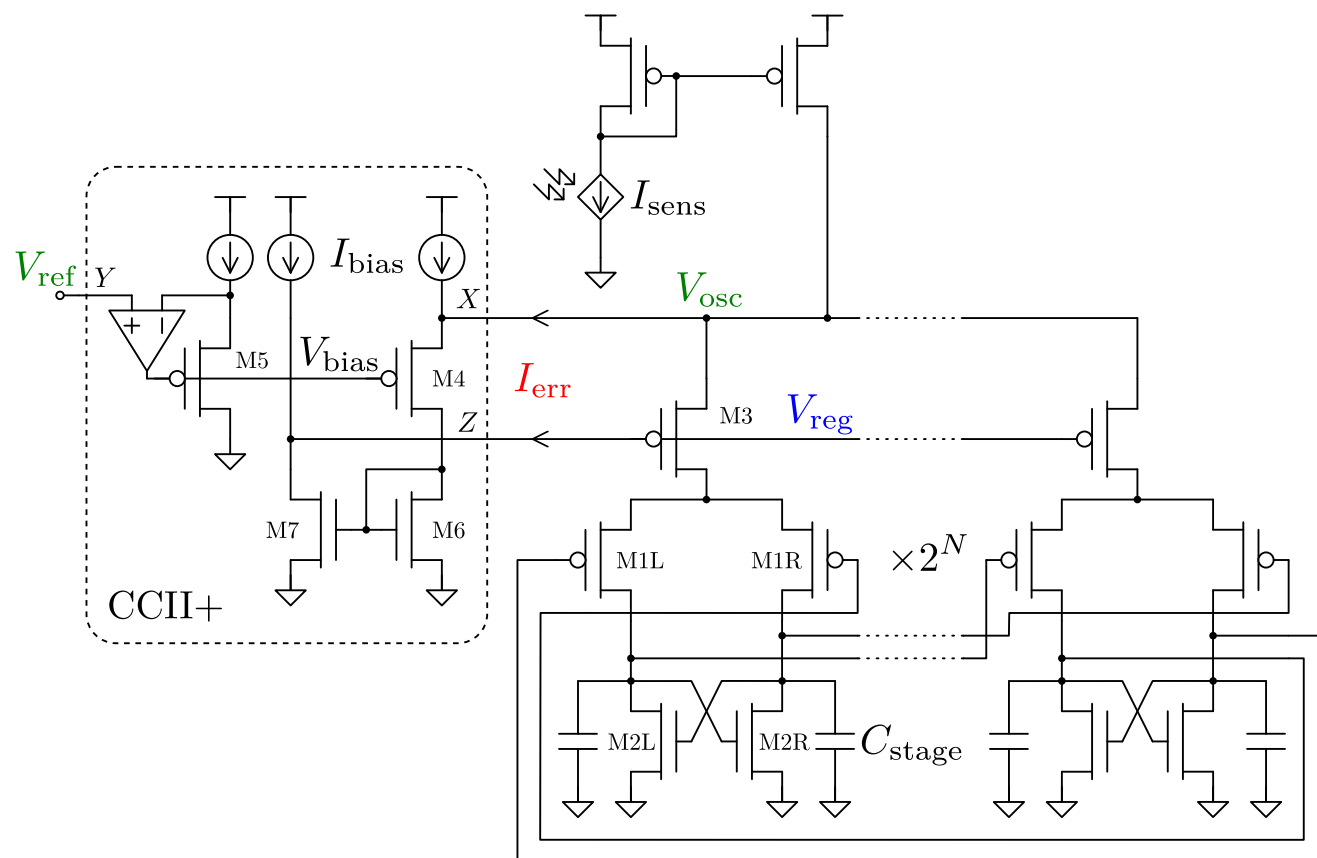
- ▶ Control of M3 transistors is **ROLLING** along the ring like I_{sens}

$$\begin{bmatrix} I_Y \\ V_X \\ I_Z \end{bmatrix} = \begin{bmatrix} 0 & 0 & 0 \\ 1 & 0 & 0 \\ 0 & 1 & 0 \end{bmatrix} \begin{bmatrix} V_Y \\ I_X \\ V_Z \end{bmatrix} \quad \left\{ \begin{array}{l} V_{osc} \leftarrow V_{ref} \\ I_Z \leftarrow I_{err} \quad (\rightarrow 0) \end{array} \right.$$

CMOS Circuit Implementation

► 3-stage CCII+ circuit:

- + **X-branch** to supply low input impedance and to sense error current
- + **Y-branch** to bias M4 for any PVT condition so $V_{osc} = V_{ref}$ when $I_{err} = 0$
- + **Z-branch** to apply negative-feedback control using error current

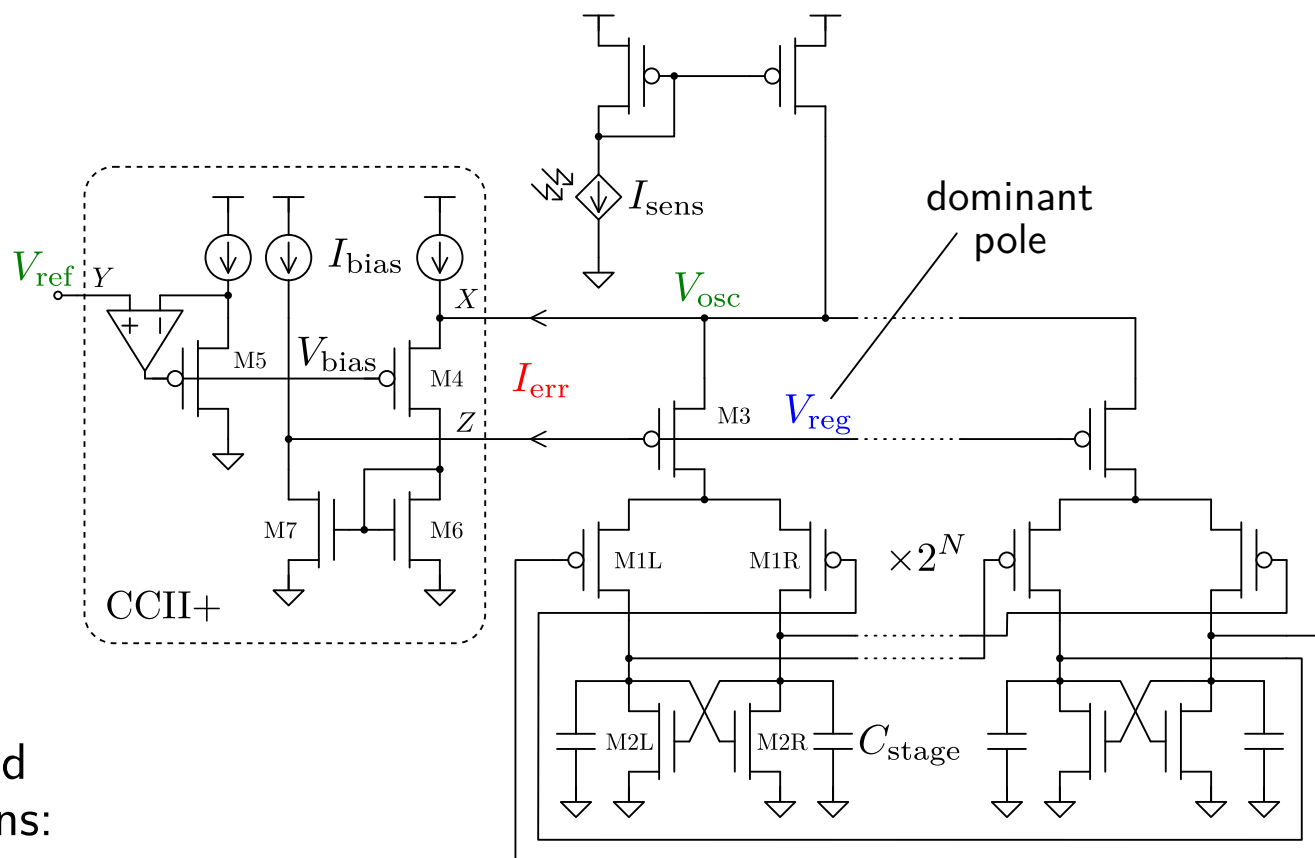


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▲ Better **stability** compared to OpAmp-based solutions:



$$r_{in} \doteq \frac{v_{osc}}{i_{sens}} \simeq \frac{1}{g_{ms3} + \frac{g_{ms4}}{1 + \frac{g_{md4}}{g_{mg6}}} \left(1 + \frac{g_{mg3}}{g_{md7}}\right)} \simeq \left(n \frac{g_{md7}}{g_{ms4}}\right) \frac{1}{g_{ms3}}$$

▲ Rail-voltage **low sensitivity** respect to signal current

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Application Example

▶ MEMS **temperature** monitoring

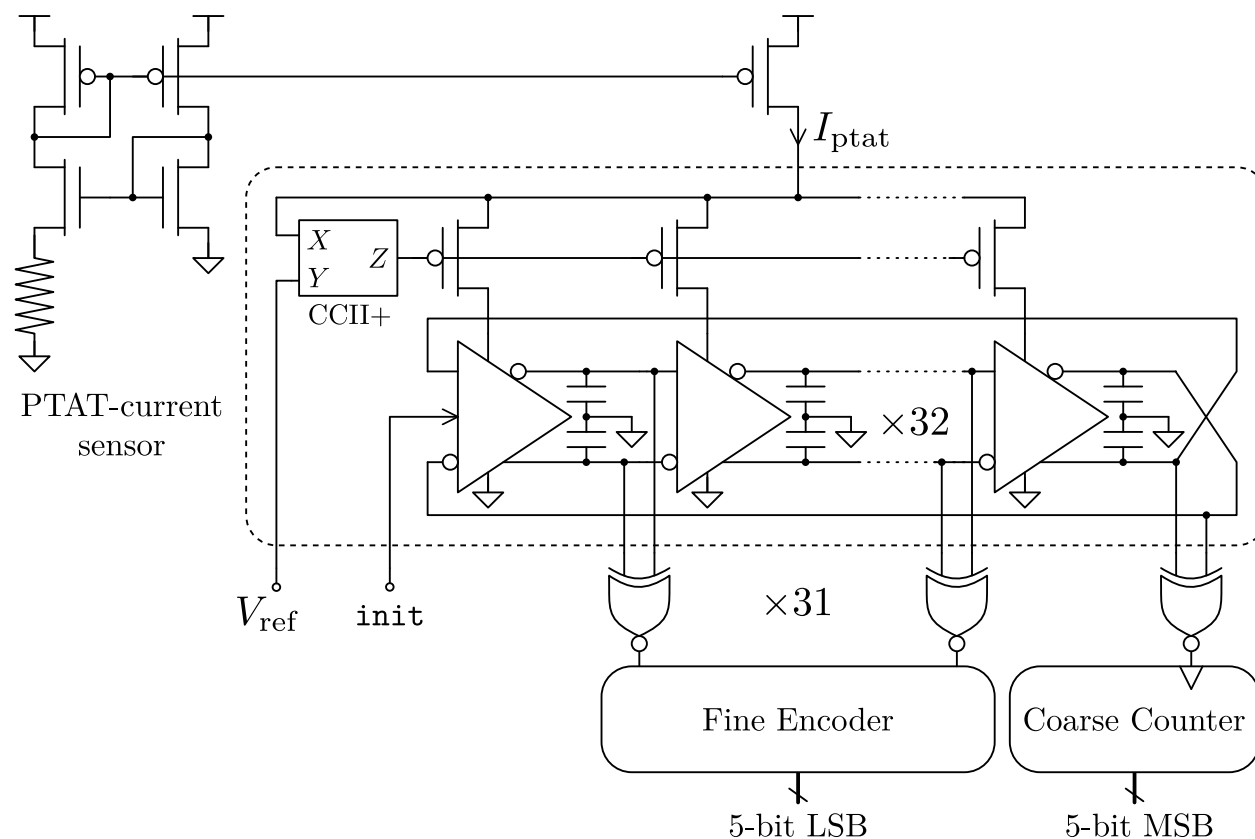
▶ CMOS **PTAT** reference operating in weak inversion as temperature sensor

▶ **10-bit 100-kS/s** ADC specifications

▶ Design parameters:

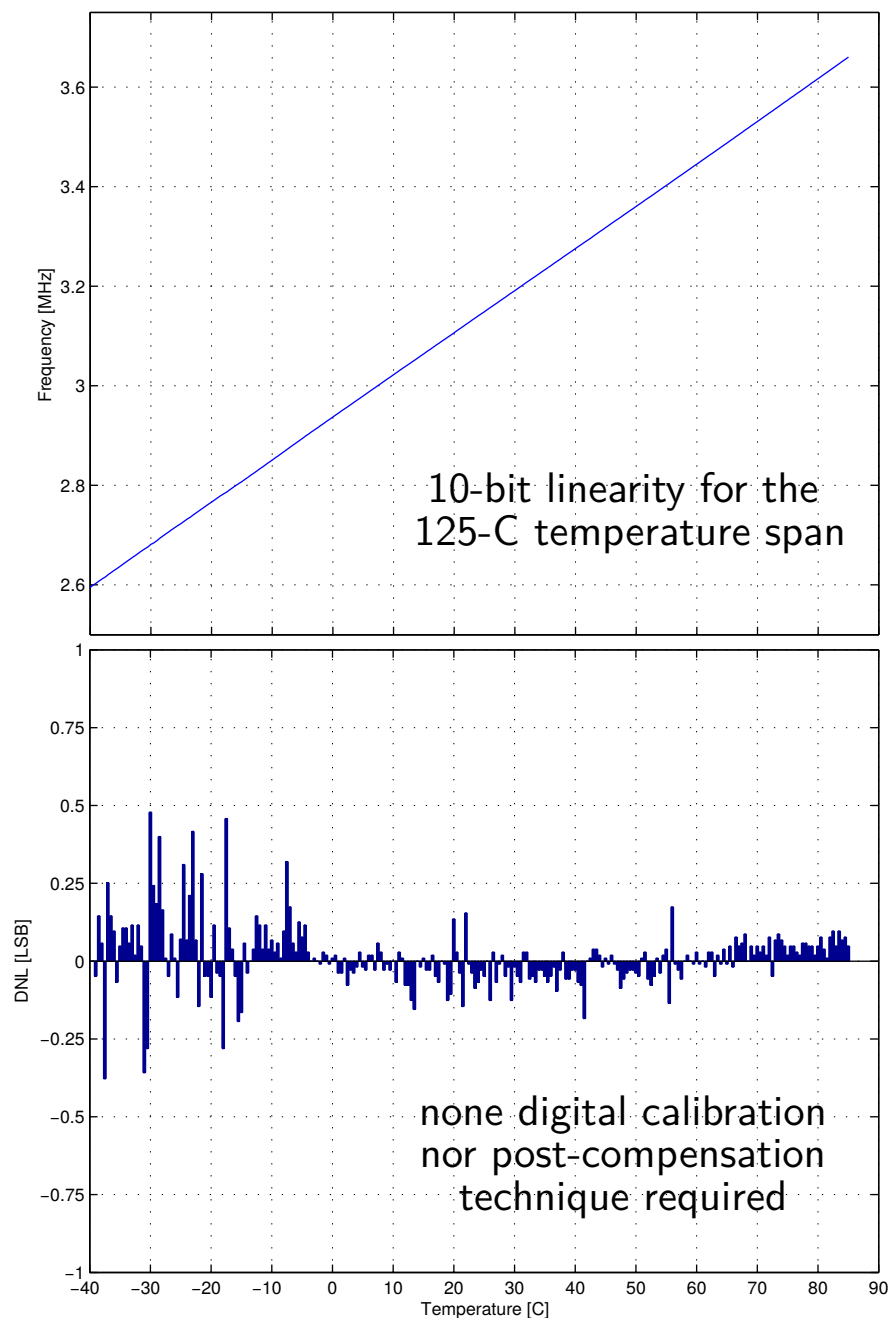
+ **5-bit/5-bit** coarse/fine quantization splitting

+ $V_{osc} = 1.4V$
 $C_{stage} = 20fF$
 $I_{ptat} = 5\mu A$ at 300K
 $f_{osc} < 4MHz$



Application Example

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 - + $f_{\text{osc}} < 4\text{MHz}$
- ▲ **70- μW** (at 1.8-V) power consumption



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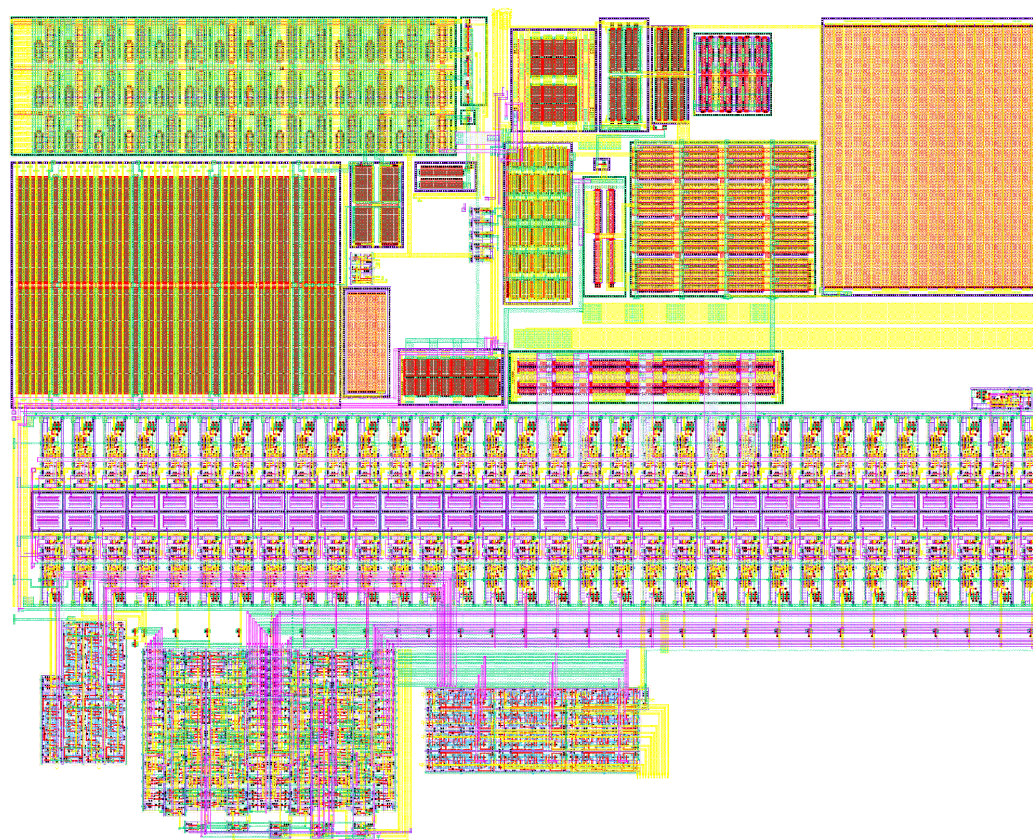
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250 μm x 200 μm (0.05mm²)



...currently being integrated in 0.18- μm 1P6M CMOS technology.

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Conclusions

- ▶ A **highly linear** I-to-F current-steering **CCRO** has been presented for ADC
- ▶ Based on rail-voltage **distributed regulation** concept
- ▶ Usage of **current conveyors** to improve loop **stability**
- ▶ **10-bit** 100-kS/s **ADC example** in 0.18- μm 1P6M CMOS technology
- ▶ Performance achieved **without** digital calibration nor post-compensation

**Thanks for
your attention!**

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